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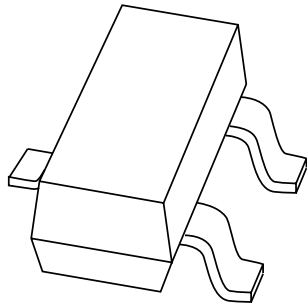
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via [salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# DATA SHEET



## **PMBD6050** High-speed diode

Product data sheet  
Supersedes data of 1999 May 11

2004 Jan 14

# High-speed diode

# PMBD6050

### FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

### APPLICATIONS

- High-speed switching in thick and thin-film circuits.

### DESCRIPTION

The PMBD6050 is a high-speed switching diode fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

### MARKING

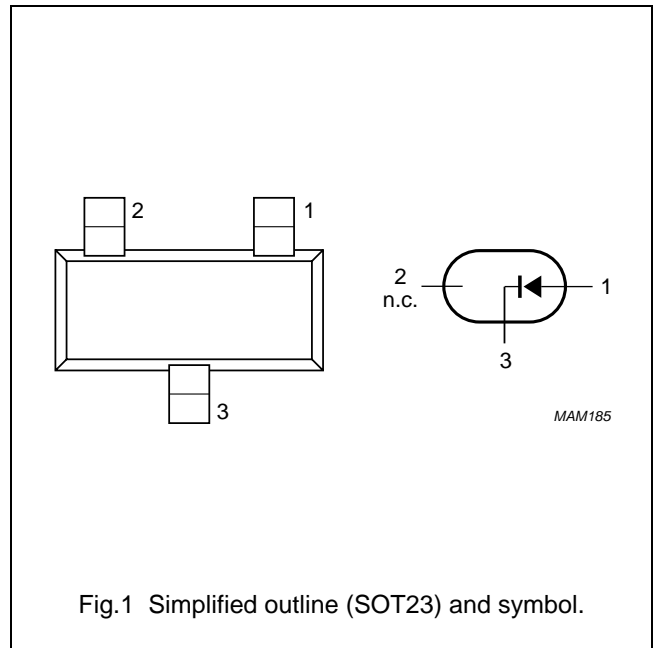
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PMBD6050	*5A

### Note

- \* = p : Made in Hong Kong.  
 \* = t : Made in Malaysia.  
 \* = W : Made in China.

### PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBD6050	–	plastic surface mounted package; 3 leads	SOT23

## High-speed diode

## PMBD6050

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage		–	85	V
$V_R$	continuous reverse voltage		–	70	V
$I_F$	continuous forward current	note 1; see Fig.2	–	215	mA
$I_{FRM}$	repetitive peak forward current		–	500	mA
$I_{FSM}$	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4			
		$t = 1\ \mu\text{s}$	–	4	A
		$t = 1\ \text{ms}$	–	1	A
		$t = 1\ \text{s}$	–	0.5	A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$ ; note 1	–	250	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

**Note**

1. Device mounted on an FR4 printed-circuit board.

## High-speed diode

## PMBD6050

**ELECTRICAL CHARACTERISTICS**

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$V_F$	forward voltage	see Fig.3 $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$ $I_F = 50\text{ mA}$ $I_F = 150\text{ mA}$	715 855 1 1.25	mV mV V V
$I_R$	reverse current	see Fig.5 $V_R = 50\text{ V}$ $V_R = 50\text{ V}; T_j = 150\text{ }^\circ\text{C}$	100 50	nA $\mu\text{A}$
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 0$ ; see Fig.6	1.5	pF
$t_{rr}$	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$ ; $R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$ ; see Fig.7	4	ns
$V_{fr}$	forward recovery voltage	when switched from $I_F = 10\text{ mA}$ ; $t_r = 20\text{ ns}$ ; see Fig.8	1.75	V

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-tp)}$	thermal resistance from junction to tie-point		330	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

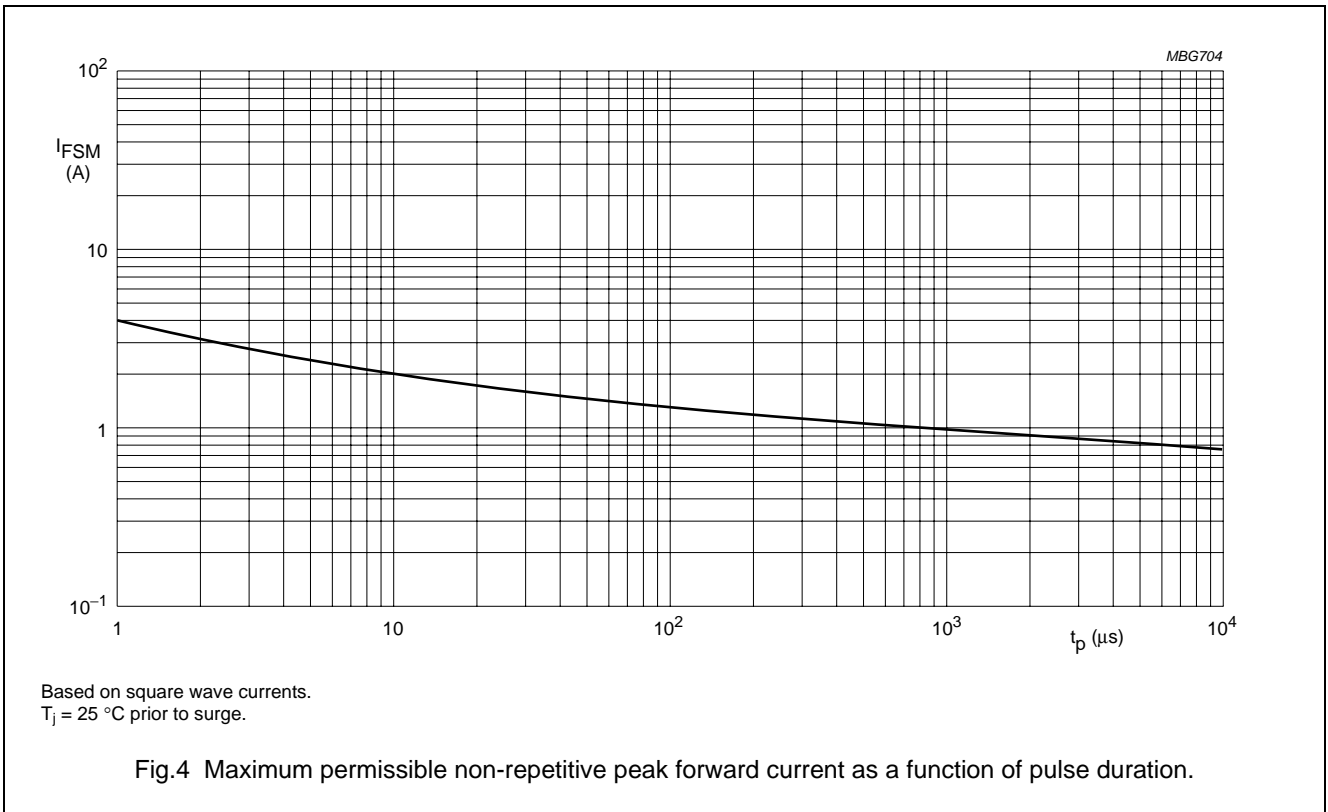
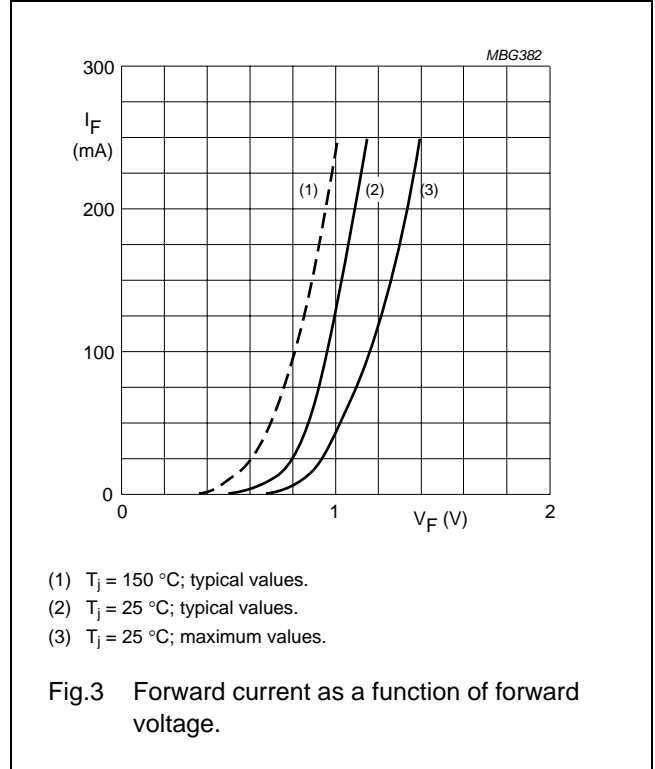
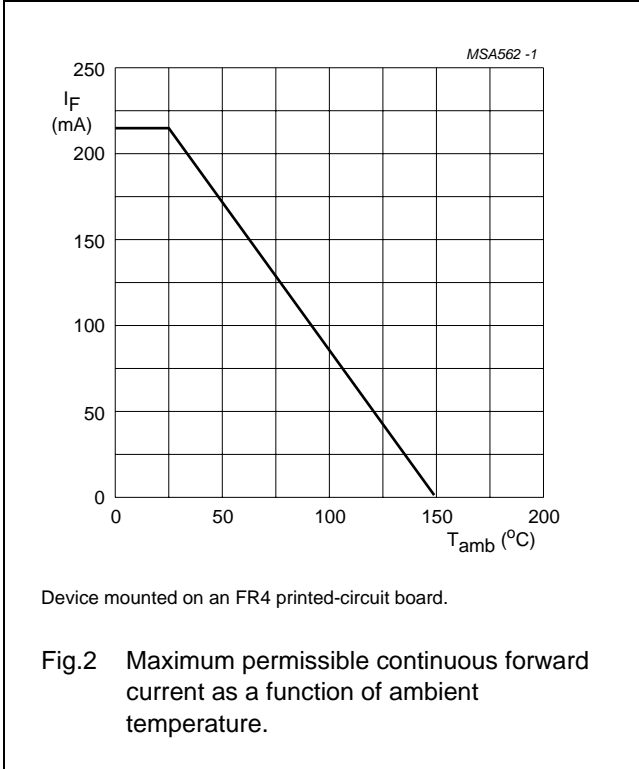
**Note**

1. Device mounted on an FR4 printed-circuit board.

# High-speed diode

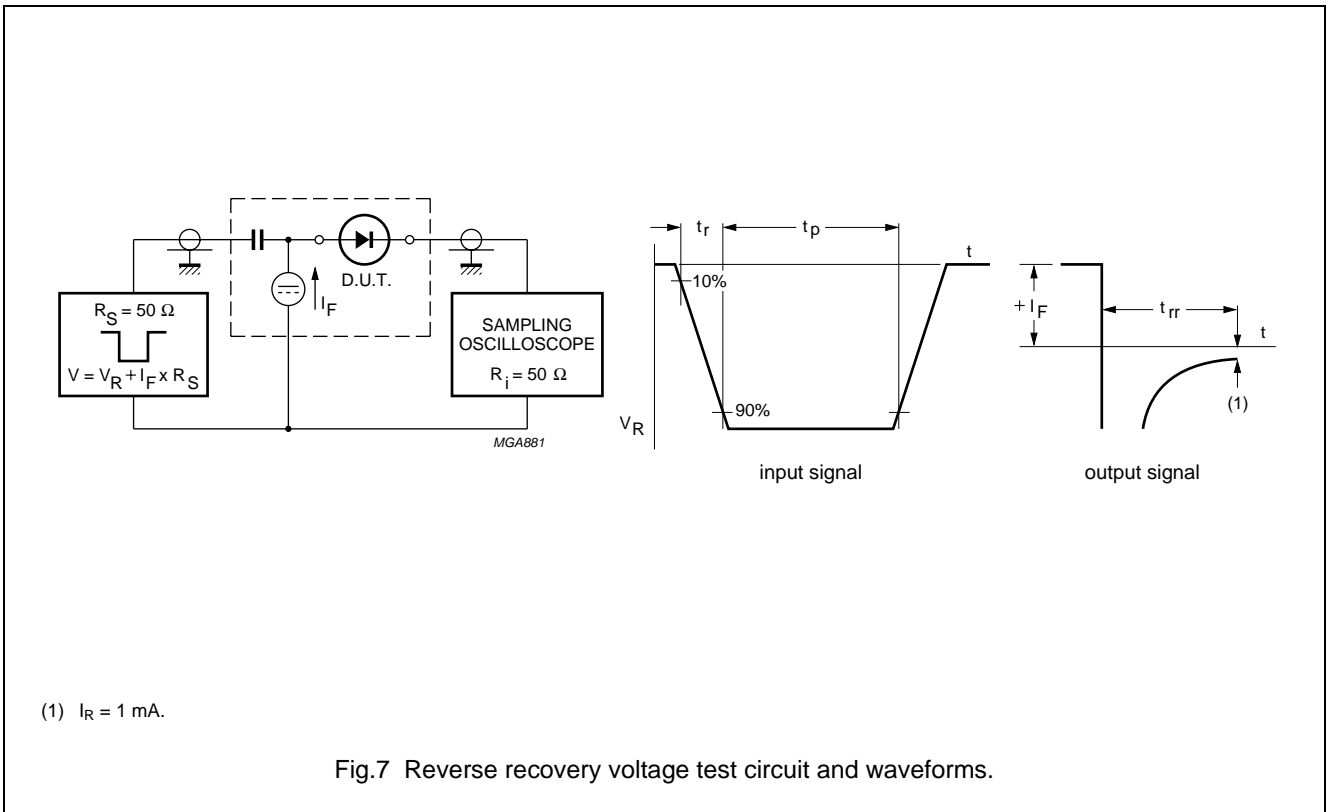
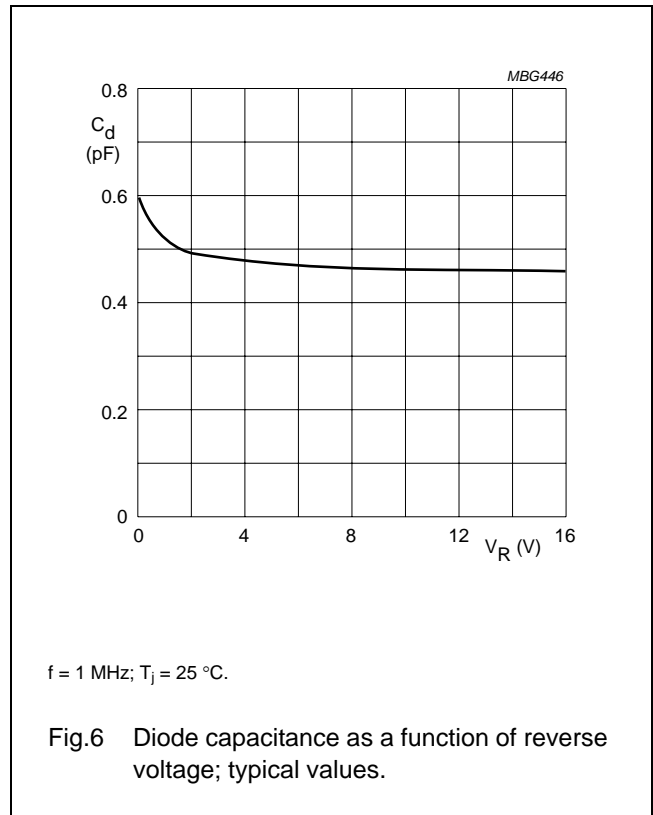
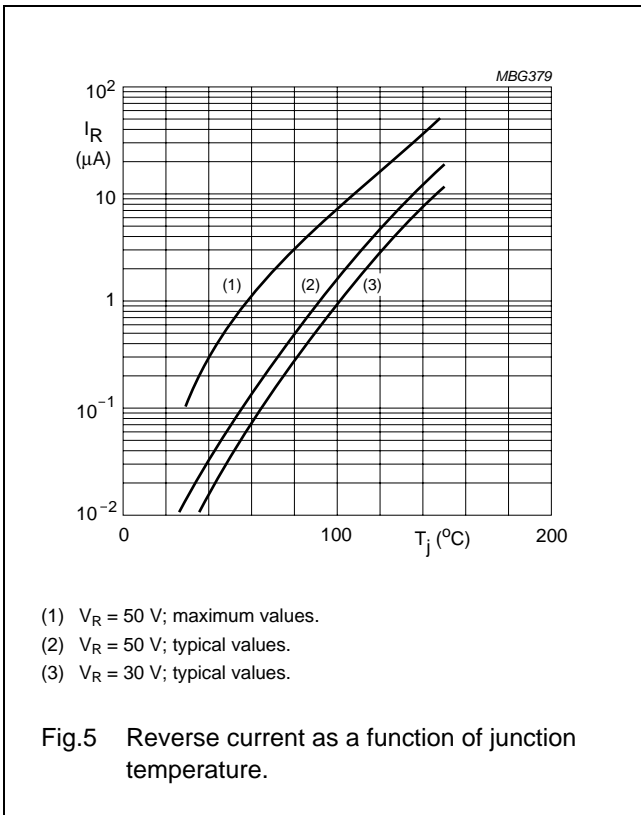
# PMBD6050

## GRAPHICAL DATA



High-speed diode

PMBD6050



High-speed diode

PMBD6050

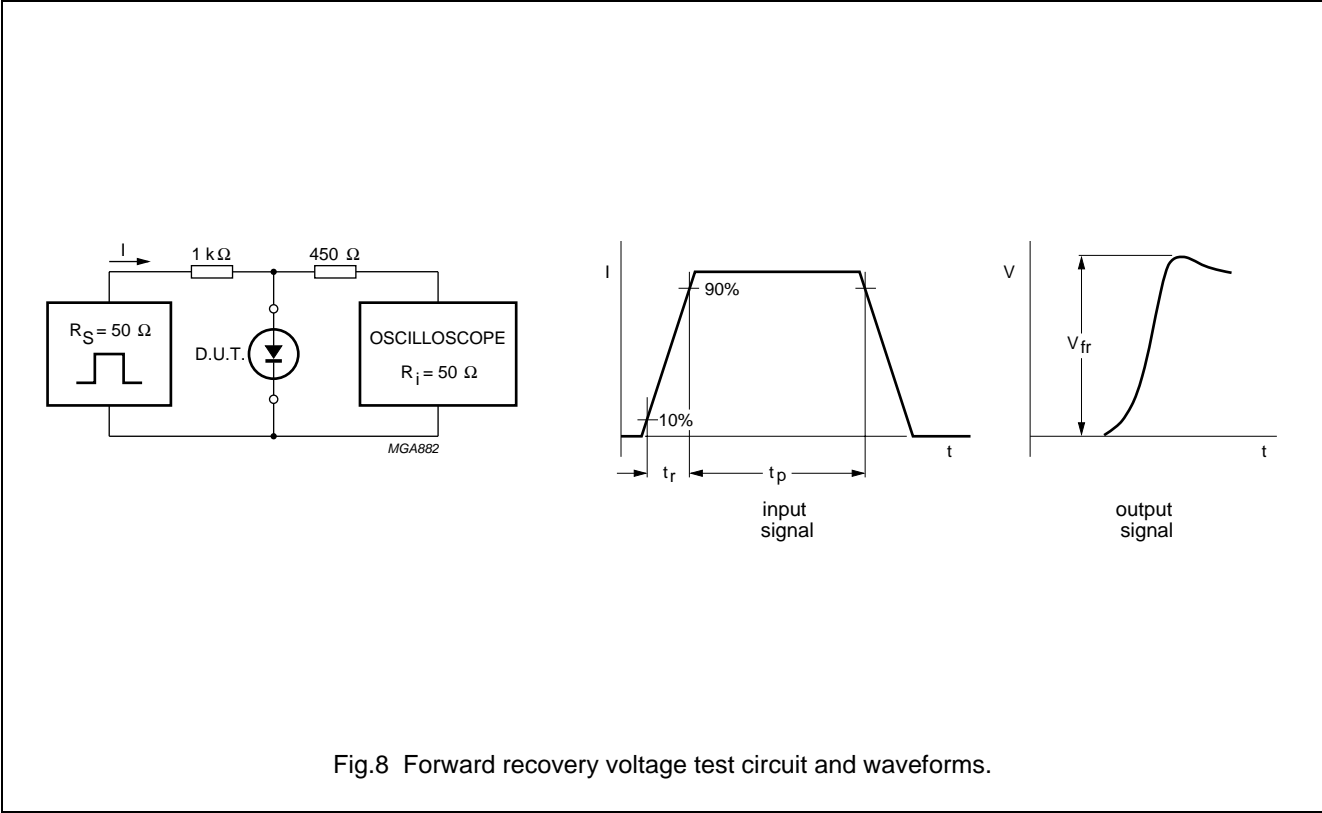


Fig.8 Forward recovery voltage test circuit and waveforms.



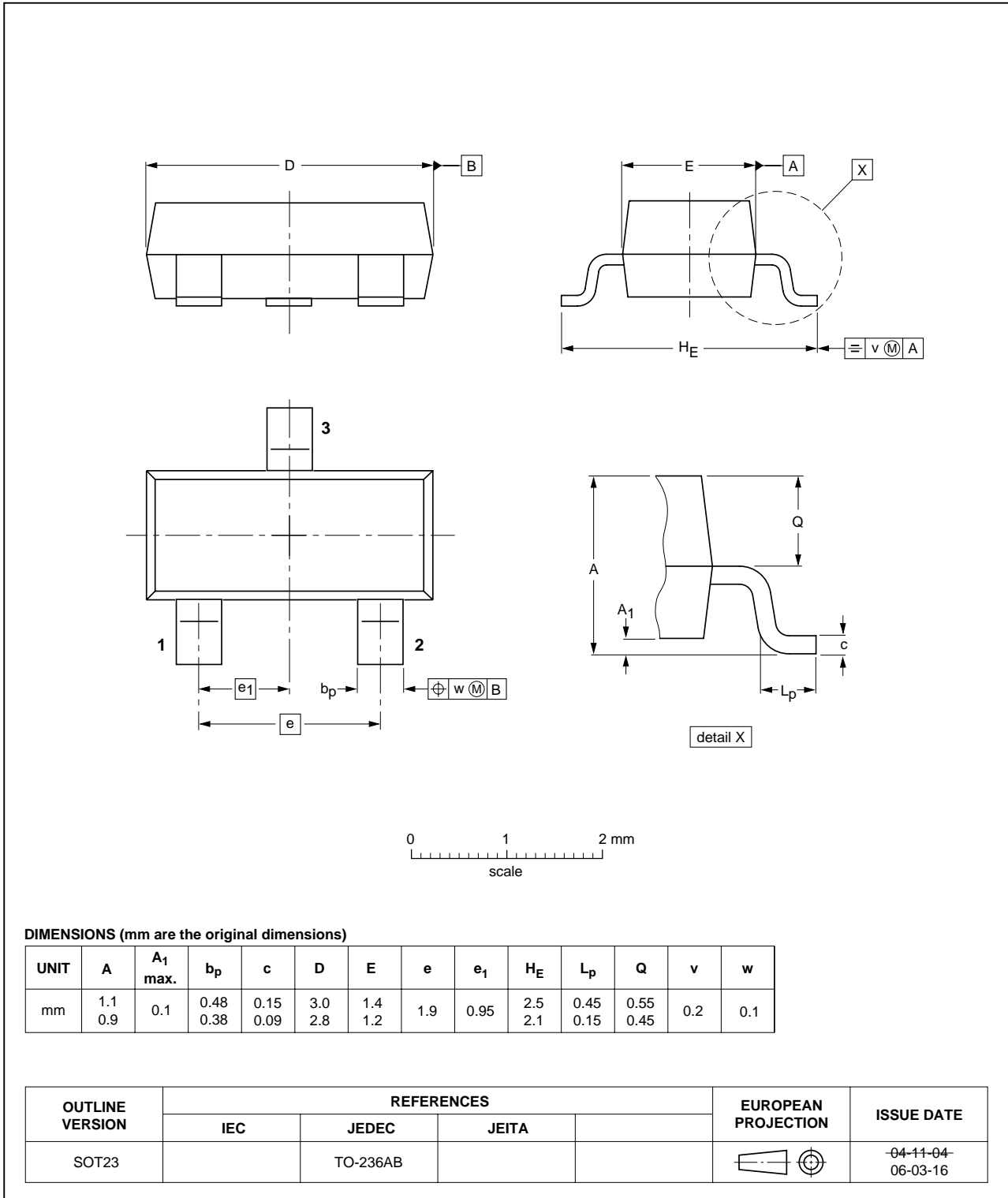
High-speed diode

PMBD6050

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



# High-speed diode

# PMBD6050

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

### Notes

1. Please consult the most recently issued document before initiating or completing a design.
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# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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